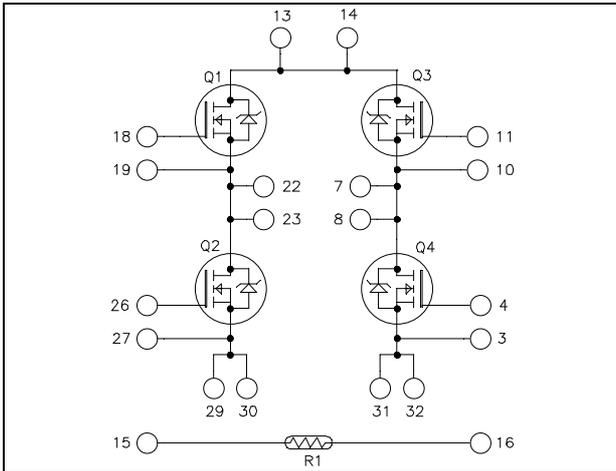


**Full - Bridge
Super Junction MOSFET
Power Module**

$V_{DSS} = 900V$
 $R_{DSon} = 60m\Omega \text{ max @ } T_j = 25^\circ C$
 $I_D = 59A \text{ @ } T_c = 25^\circ C$

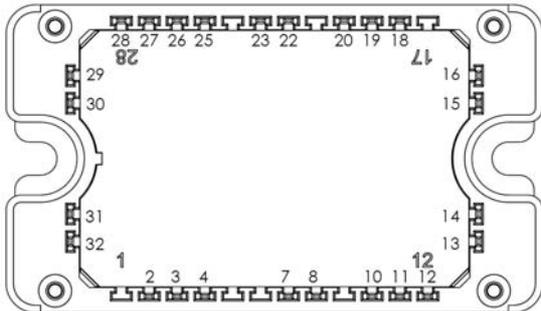


Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- **Super junction MOSFET**
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring



Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23 ...

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings (per super junction MOSFET)

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Voltage	900	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	59
		$T_c = 80^\circ C$	44
I_{DM}	Pulsed Drain current	150	A
V_{GS}	Gate - Source Voltage	± 20	V
R_{DSon}	Drain - Source ON Resistance	60	$m\Omega$
P_D	Power Dissipation	$T_c = 25^\circ C$	462
I_{AR}	Avalanche current (repetitive and non repetitive)	8.8	A
E_{AR}	Repetitive Avalanche Energy	2.9	mJ
E_{AS}	Single Pulse Avalanche Energy	1940	

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics (per super junction MOSFET)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} = 0V, V _{DS} = 900V			200	μA
R _{DS(on)}	Drain – Source on Resistance	V _{GS} = 10V, I _D = 52A		50	60	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 6mA	2.5	3	3.5	V
I _{GSS}	Gate – Source Leakage Current	V _{GS} = ±20 V, V _{DS} = 0V			200	nA

Dynamic Characteristics (per super junction MOSFET)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C _{iss}	Input Capacitance	V _{GS} = 0V ; V _{DS} = 100V f = 1MHz		13.6		nF
C _{oss}	Output Capacitance			0.66		
Q _g	Total gate Charge	V _{GS} = 10V V _{Bus} = 400V I _D = 52A		540		nC
Q _{gs}	Gate – Source Charge			64		
Q _{gd}	Gate – Drain Charge			230		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) V _{GS} = 10V V _{Bus} = 600V I _D = 52A R _G = 3.8Ω		70		ns
T _r	Rise Time			20		
T _{d(off)}	Turn-off Delay Time			400		
T _f	Fall Time			25		
E _{on}	Turn-on Switching Energy	Inductive switching @ 25°C V _{GS} = 10V ; V _{Bus} = 600V I _D = 52A ; R _G = 3.8Ω		3		mJ
E _{off}	Turn-off Switching Energy			1.5		
E _{on}	Turn-on Switching Energy	Inductive switching @ 125°C V _{GS} = 10V ; V _{Bus} = 600V I _D = 52A ; R _G = 3.8Ω		4.2		mJ
E _{off}	Turn-off Switching Energy			1.7		
R _{thJC}	Junction to Case Thermal Resistance				0.27	°C/W

Source - Drain diode ratings and characteristics (per super junction MOSFET)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I _S	Continuous Source current (Body diode)	T _c = 25°C			59	A
		T _c = 80°C			44	
V _{SD}	Diode Forward Voltage	V _{GS} = 0V, I _S = - 52A		0.8	1.2	V
t _{rr}	Reverse Recovery Time	I _S = - 52A V _R = 400V di/dt = 200A/μs		920		ns
Q _{rr}	Reverse Recovery Charge		T _j = 25°C		60	

Thermal and package characteristics

Symbol	Characteristic	Min	Max	Unit		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz	4000		V		
T _J	Operating junction temperature range	-40	150	°C		
T _{JOP}	Recommended junction temperature under switching conditions	-40	T _{Jmax} -25			
T _{STG}	Storage Temperature Range	-40	125			
T _C	Operating Case Temperature	-40	125			
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

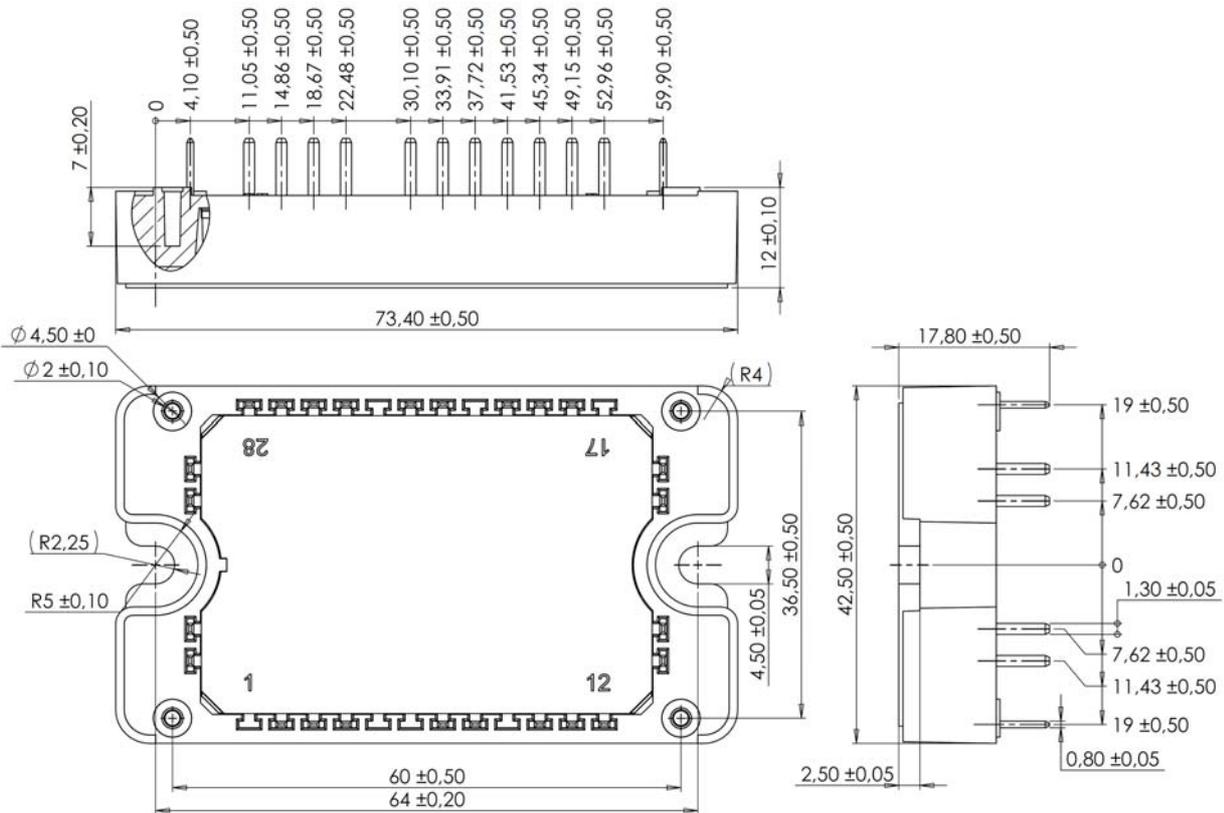
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C = 100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

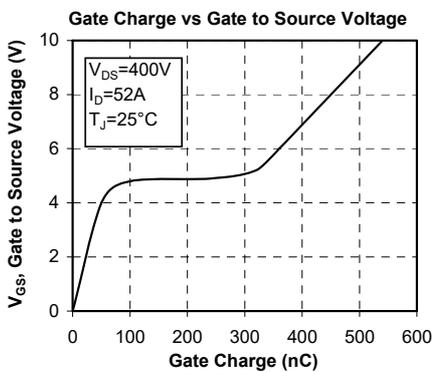
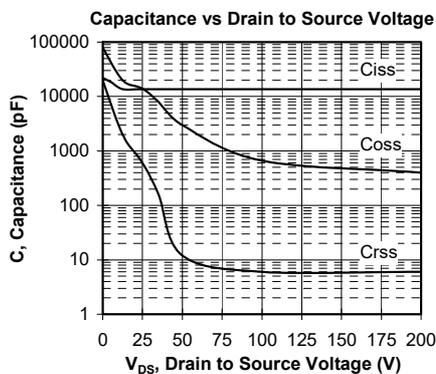
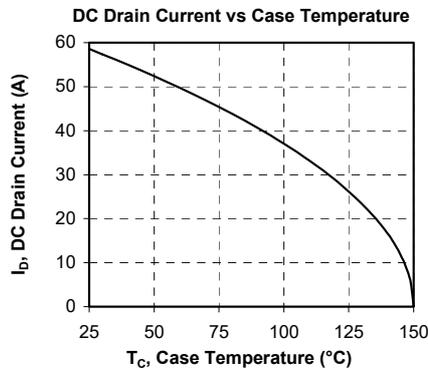
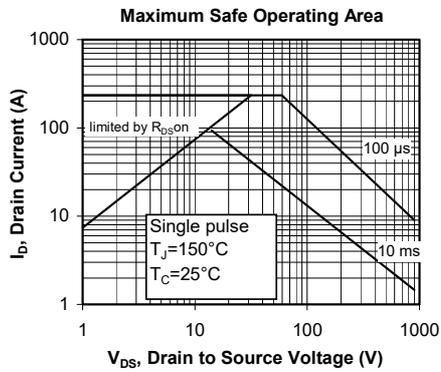
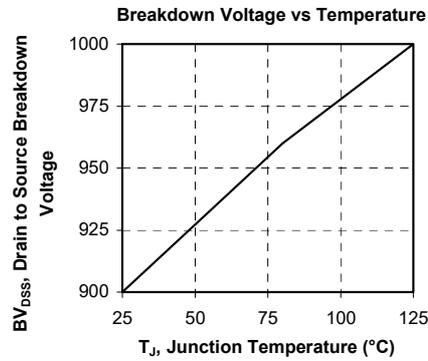
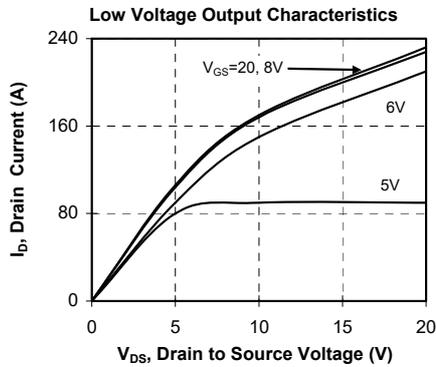
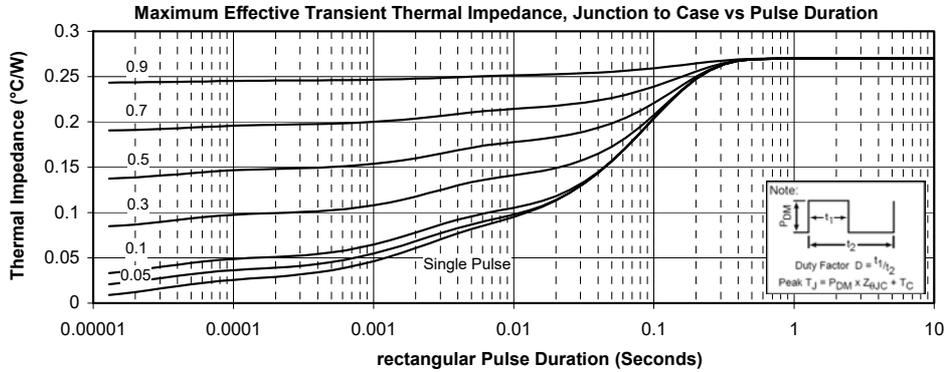
T: Thermistor temperature
 R_T: Thermistor value at T

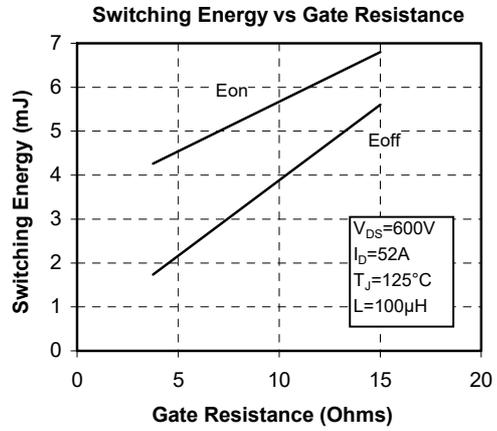
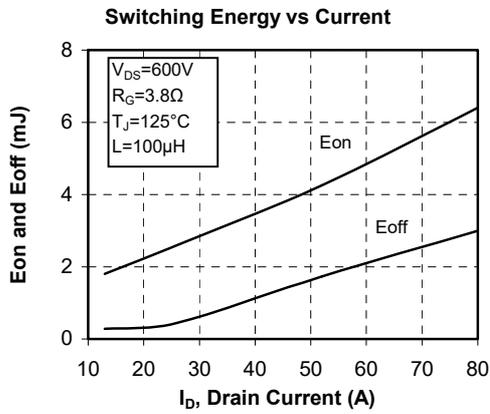
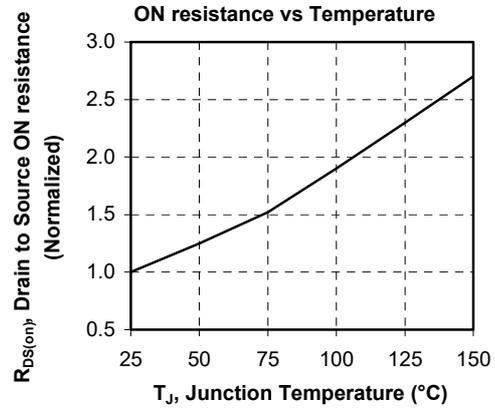
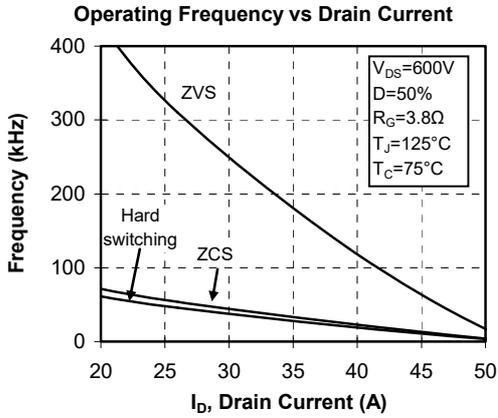
Package outline (dimensions in mm)



See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

Typical Performance Curve





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